IN THE SPECIFICATION:

Please replace the paragraph starting at line 17 on page 13 with the following paragraph:

In one version of a method of forming a coating 24 comprising a diamond like material, a component structure 25 is placed in a plasma zone 213 of a process chamber, and embodiment of which is shown in Figure 7a. The chamber 106 comprises chamber walls 218 enclosing the plasma zone 213. The component 20 can be held on a support 202 in the chamber 106. A process gas supply ~~130~~ 270 provides a deposition gas into the chamber 106, and can comprise a gas source, one or more conduits leading from the source to the chamber, flow meters, and one or more gas inlets in the chamber 106. The process gas comprises at least a carbon-containing compound, such as a carbon-containing gas, that is capable of forming bonded carbon networks in the coating 24. The process gas can also comprise a hydrogen-containing compound, such as a hydrogen-containing gas. For example, the process gas can comprise a gas comprising both carbon and hydrogen atoms, such as at least one of methane, propane, acetylene, butane and ethelyne. To form a diamond like nanocomposite comprising a network of silicon and oxygen, the process gas can further comprise a silicon-containing compound. For example, the process gas can comprise hexamethyldisiloxane or polyphenylmethylsiloxane, as described for example in U.S. Patent No 5,638,251 to Goel et al, filed on October 3, 1995 and assigned to Advanced Refractory Technologies, which is herein incorporated by reference in its entirety. The process gas can further comprise an additive gas, such as for example argon.

Please replace the paragraph starting at line 9 on page 24 with the following paragraph:

The components 20 having the contamination reducing coatings may be a part of a multi-chamber apparatus 102 comprising a plurality of processing chambers 106a-d. An embodiment of an apparatus 102 suitable for processing substrates 10 comprises one or more processing chambers 106a-d, as shown in Figure 6. The chambers 106a-d are mounted on a platform, such as an Endura 2 platform from Applied Materials, Inc., of Santa Clara, California, that provides electrical, plumbing, and other support functions. The platform ~~109~~ 110 typically supports a load lock ~~113~~ 107 to receive a cassette 115 of substrates 104 to be processed and a substrate transfer chamber 117 containing a robot 119 to transfer substrates from the cassette 115 to the different chambers 106a-d for processing and return them after processing. The different chambers 106a-d may include, for example, a cleaning chamber, an etching chamber, a deposition chamber for depositing materials on substrates, optionally, a heat treatment chamber, and other processing chambers. For example, in one version, one of the chambers 106a-d comprises a heat treatment chamber comprising a heating pedestal 151 to heat the substrate 104 before processing to degas the substrate 104. After degassing of the substrate 104, the substrate 104 can be transferred by the robot 119 to a process chamber 106 to etch material on the substrate 104. The substrate 104 can also be transferred by the robot 119 to a process chamber comprising a deposition chamber, for example to deposit a barrier layer onto a substrate 104 held on an electrostatic chuck. After processing, the substrate 104 can be transferred by the robot 119 to a cool-down chamber where the substrate can be placed on a cooling pedestal 152 to cool the substrate 104. The chambers 106a-d are interconnected to form a continuous vacuum environment within the apparatus 102 in which the process may proceed uninterrupted, thereby reducing contamination of substrates 104 that may otherwise occur when transferring wafers between separate chambers for different process stages. The components in the apparatus 102, such as

components that contact or support the substrate 104, also desirably comprise contamination reducing materials to reduce the contamination of the substrate 104.

Please replace the paragraph starting at line 1 on page 25 with the following paragraph:

An embodiment of a process chamber 106 which may comprise the components 20 having the contamination-reducing material is shown in Figure 7b. The chamber 106 comprises an enclosure wall 118, which may comprise a ceiling, sidewalls, and a bottom wall that enclose a process zone 113. In operation, process gas is introduced into the chamber 106 through a gas supply 130 that includes a process gas source, and a gas distributor. The gas distributor may comprise one or more conduits having one or more gas flow valves and one or more gas outlets around a periphery of the substrate 104 which may be held in the process zone ~~111~~ 113 on the substrate support 100 having a substrate receiving surface ~~180~~ 121. Alternatively, the gas distributor may comprise a showerhead gas distributor (not shown). Spent process gas and process byproducts are exhausted from the chamber 106 through an exhaust 120 which may include an exhaust conduit that receives spent process gas from the process zone 113, a throttle valve to control the pressure of process gas in the chamber 106, and one or more exhaust pumps.

Please replace the paragraph starting at line 33 on page 25 with the following paragraph:

To process a substrate 104, the process chamber 106 is evacuated and maintained at a predetermined sub-atmospheric pressure. The substrate 104 is then provided on the support 100 by a substrate transport, such as for example a robot arm 103 and a lift pin 160. The substrate 104 can be held on the support 100 by applying a voltage to the electrode 108 in the support 100, for example via an electrode power supply 172. The gas supply ~~130~~ 170 provides a process gas to the chamber 106 and

the gas energizer 116 couples RF or microwave energy to the process gas to energizes the gas to process the substrate 104. Effluent generated during the chamber process is exhausted from the chamber 106 by the exhaust 120.

Please replace the paragraph starting at line 7 on page 26 with the following paragraph:

The chamber 106 and multi-chamber apparatus 101 can be controlled by a controller 194 that comprises program code having instruction sets to operate components of each chamber 106a-d to process substrates 104 in the chamber 106, as shown for example in Figure 7b. For example, the controller 194 can comprise a substrate positioning instruction set to operate one or more of the substrate support 100 and robot arm 119 and lift pins 160 to position a substrate 104 in the chamber 106; a gas flow control instruction set to operate the gas supply ~~130~~ 170 and flow control valves to set a flow of gas to the chamber 106; a gas pressure control instruction set to operate the exhaust 120 and throttle valve to maintain a pressure in the chamber 106; a gas energizer control instruction set to operate the gas energizer 116 to set a gas energizing power level; a temperature control instruction set to control temperatures in the chamber 106; and a process monitoring instruction set to monitor the process in the chamber 106.

IN THE DRAWINGS:

Please replace Figure 6, 7A and 7B with the enclosed amended drawings.

On Figure 6, reference number 109 has been replaced with 110, and reference number 113 has been replaced with 107.

On Figure 7A, reference number 230 has been replaced with 270.

On Figure 7B, reference number 130 has been replaced with 170, and reference number 121 has been added.